

# XP05553

## Silicon NPN epitaxial planar transistor

For low-frequency amplification

### ■ Features

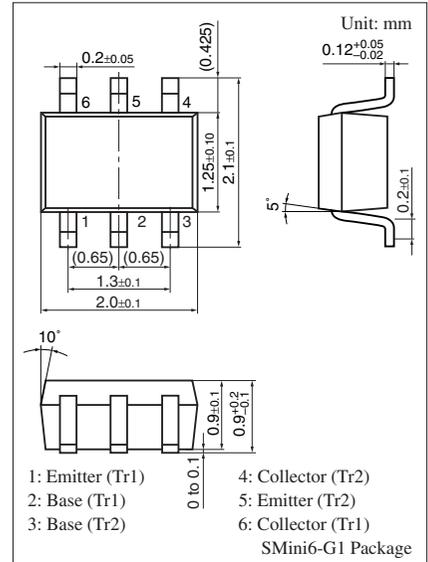
- Two elements incorporated into one package (Each transistor is separated)
- Reduction of the mounting area and assembly cost by one half
- High forward current transfer ratio  $h_{FE}$

### ■ Basic Part Number of Element

- 2SD1149 × 2 elements

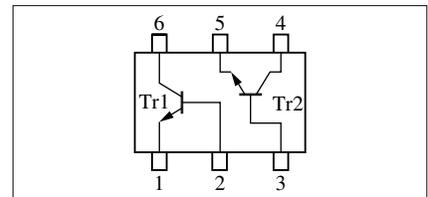
### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Rating of element	Collector-base voltage (Emitter open)	$V_{CBO}$	100	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	100	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	15	V
	Collector current	$I_C$	20	mA
Overall	Total power dissipation	$P_T$	150	mW
	Junction temperature	$T_j$	150	$^\circ\text{C}$
	Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



Marking Symbol: 4U

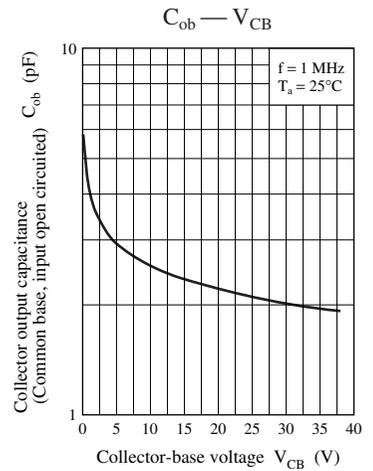
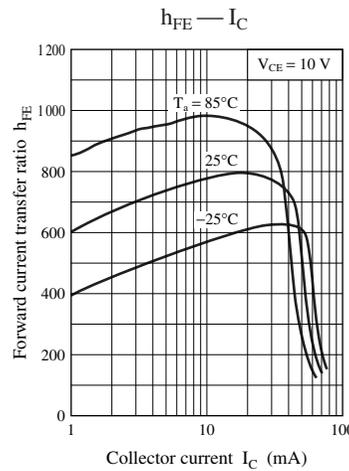
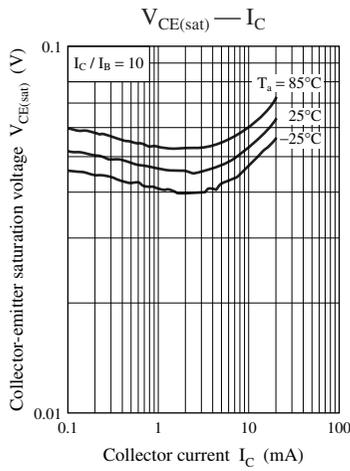
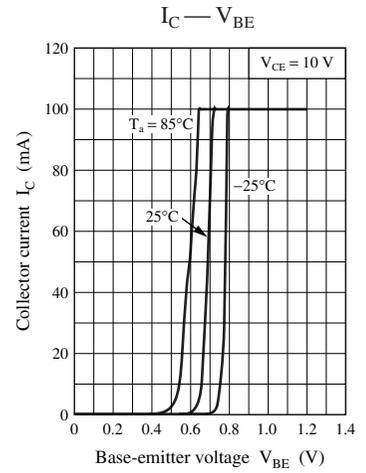
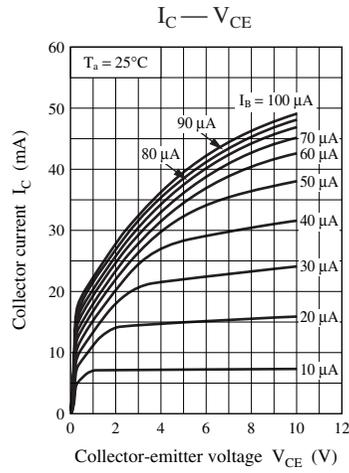
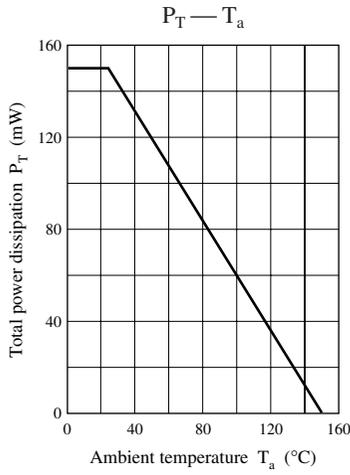
Internal Connection



### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	100			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	100			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	15			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 60 \text{ V}, I_E = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 60 \text{ V}, I_B = 0$			1	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	400		2000	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$		0.05	0.20	V
Noise voltage	NV	$V_{CE} = 10 \text{ V}, I_C = 1 \text{ mA}, G_V = 80 \text{ dB}$ $R_g = 100 \text{ k}\Omega, \text{Function} = \text{Flat}$		80		mV
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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